

100V N-Ch Power MOSFET

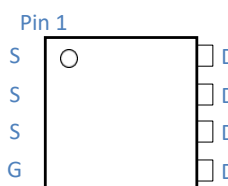
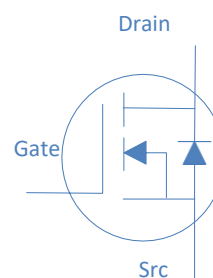
Features:

- ◇ High Speed Power Switching
- ◇ Enhanced Body diode dv/dt capability
- ◇ Enhanced Avalanche Ruggedness
- ◇ 100% UIS Tested, 100% Rg Tested
- ◇ Lead Free, Halogen Free

Application:

- ◇ Synchronous Rectification in SMPS
- ◇ Hard Switching and High Speed Circuit
- ◇ DC/DC in Telecoms and Industrial

DFN5*6



Part Number	Package	Marking
KPRGN120N10A	DFN5*6	GN120N10A

V_{DS}	100	V
$R_{DS(on),typ}$	12.0	mΩ
I_D (Silicon limited)	50.8	A
I_D (Package limited)	45	A

Absolute Maximum Ratings at $T_J=25^{\circ}\text{C}$ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	$T_C=25^{\circ}\text{C}$	51	A
		$T_C=100^{\circ}\text{C}$	32	
		$T_C=25^{\circ}\text{C}$	45	
Continuous Drain Current (Package Limited)				
Drain to Source Voltage	V_{DS}	-	100	V
Gate to Source Voltage	V_{GS}	-	± 20	V
Pulsed Drain Current	I_{DM}	-	150	A
Avalanche Energy, Single Pulse	E_{AS}	$L=0.1\text{mH}$, $T_C=25^{\circ}\text{C}$	20	mJ
Power Dissipation	P_D	$T_C=25^{\circ}\text{C}$	66	W
Operating and Storage Temperature	T_J , T_{stg}	-	-55 to 150	$^{\circ}\text{C}$

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	60	$^{\circ}\text{C/W}$
Thermal Resistance Junction-Case	$R_{\theta JC}$	1.9	$^{\circ}\text{C/W}$

Electrical Characteristics at $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Static Characteristics

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}$, $I_D=250\mu\text{A}$	2.0	3.0	4.0	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0\text{V}$, $V_{DS}=100\text{V}$, $T_j=25^{\circ}\text{C}$	-	-	1	μA
		$V_{GS}=0\text{V}$, $V_{DS}=100\text{V}$, $T_j=100^{\circ}\text{C}$	-	-	100	
Gate to Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$	-	-	± 100	nA
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$, $I_D=20\text{A}$	-	12	13	m Ω
Transconductance	g_{fs}	$V_{DS}=5\text{V}$, $I_D=20\text{A}$	-	37	-	S
Gate Resistance	R_G	$V_{GS}=0\text{V}$, V_{DS} Open, $f=1\text{MHz}$	-	1.4	-	Ω

Dynamic Characteristics

Input Capacitance	C_{iss}	$V_{GS}=0\text{V}$, $V_{DS}=50\text{V}$, $f=1\text{MHz}$	-	1360	-	pF
Output Capacitance	C_{oss}		-	200	-	
Reverse Transfer Capacitance	C_{rss}		-	7.5	-	
Total Gate Charge	$Q_g(10\text{V})$	$V_{DD}=50\text{V}$, $I_D=20\text{A}$, $V_{GS}=10\text{V}$	-	20	-	nC
Gate to Source Charge	Q_{gs}		-	7	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	3.5	-	
Turn on Delay Time	$t_{d(on)}$	$V_{DD}=50\text{V}$, $I_D=20\text{A}$, $V_{GS}=10\text{V}$, $R_G=10\Omega$,	-	6	-	ns
Rise time	t_r		-	3	-	
Turn off Delay Time	$t_{d(off)}$		-	17	-	
Fall Time	t_f		-	3	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}$, $I_F=20\text{A}$	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R=50\text{V}$, $I_F=20\text{A}$, $dI_F/dt=500\text{A}/\mu\text{s}$	-	45	-	ns
Reverse Recovery Charge	Q_{rr}		-	175	-	nC

Fig 1. Typical Output Characteristics

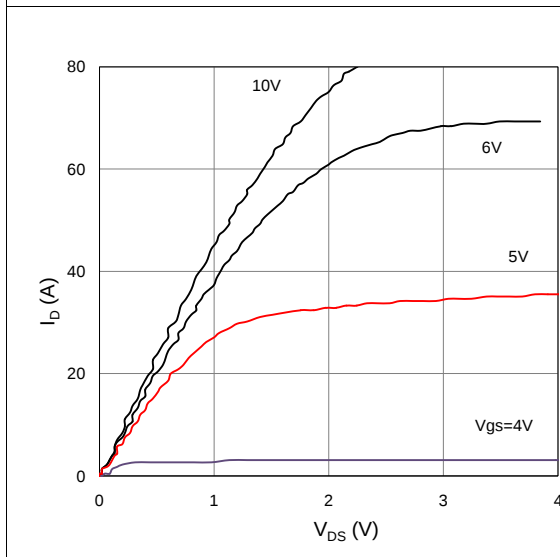


Figure 2. On-Resistance vs. Gate-Source Voltage

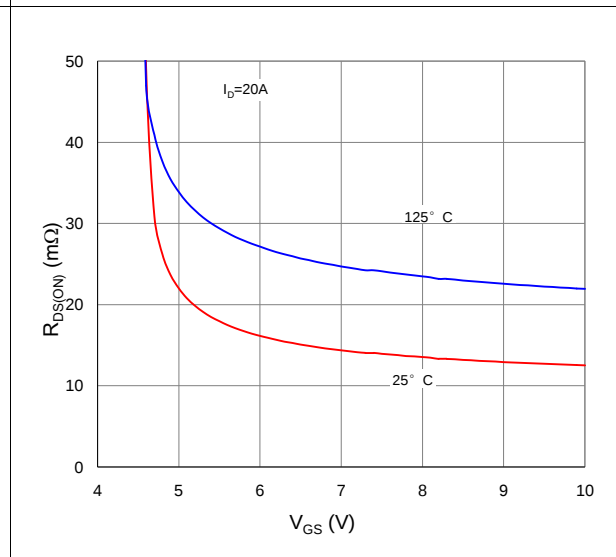


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

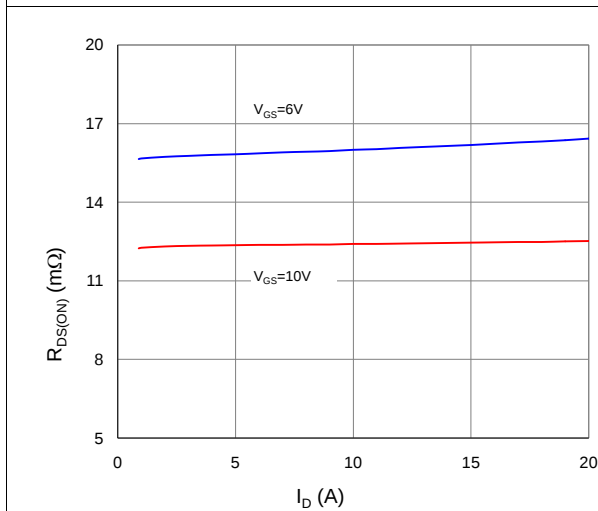


Figure 4. Normalized On-Resistance vs. Junction Temperature

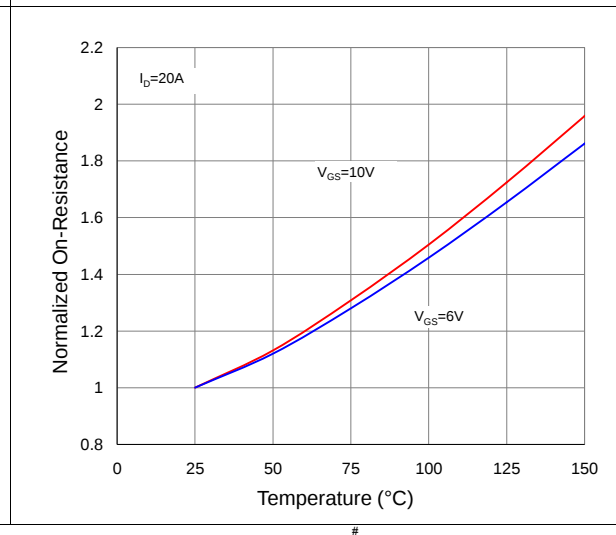


Figure 5. Typical Transfer Characteristics

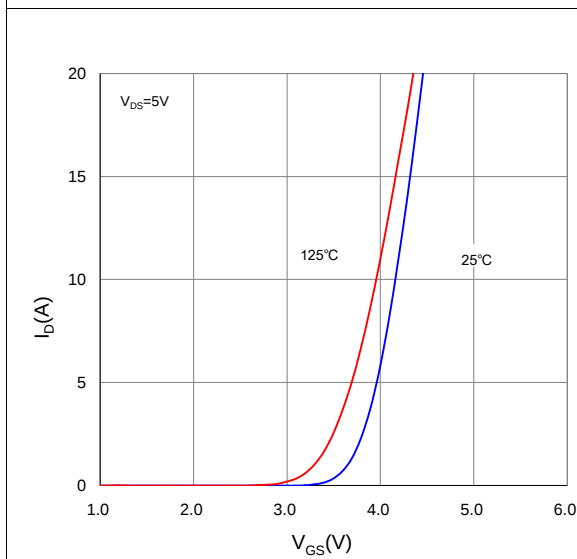


Figure 6. Typical Source-Drain Diode Forward Voltage

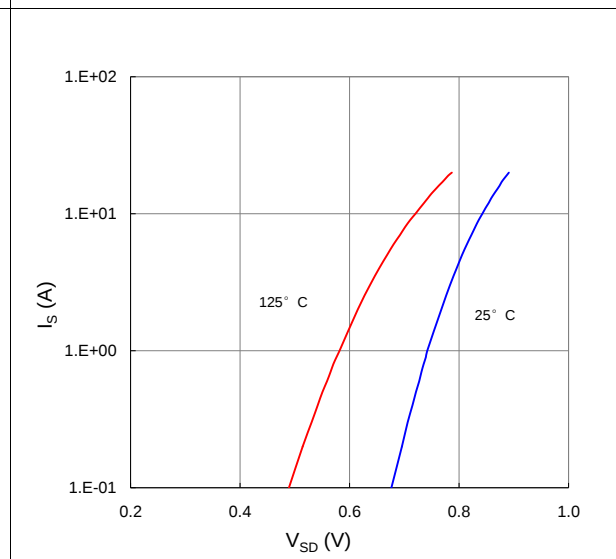


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

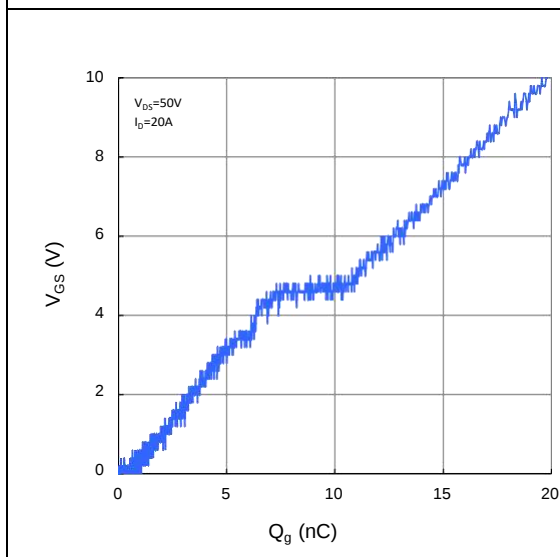


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

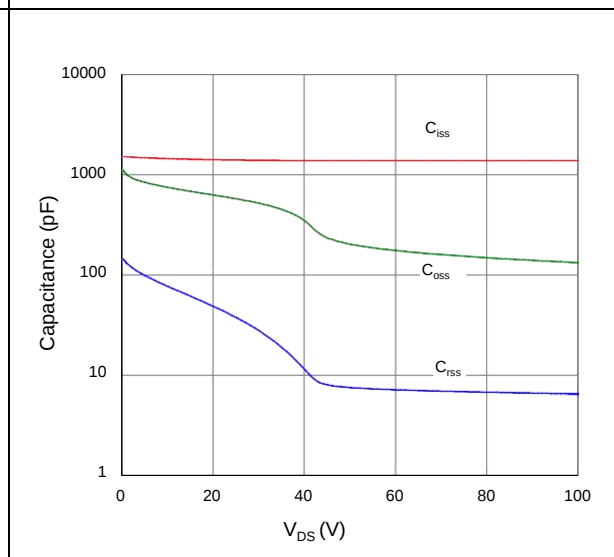


Figure 9. Maximum Safe Operating Area

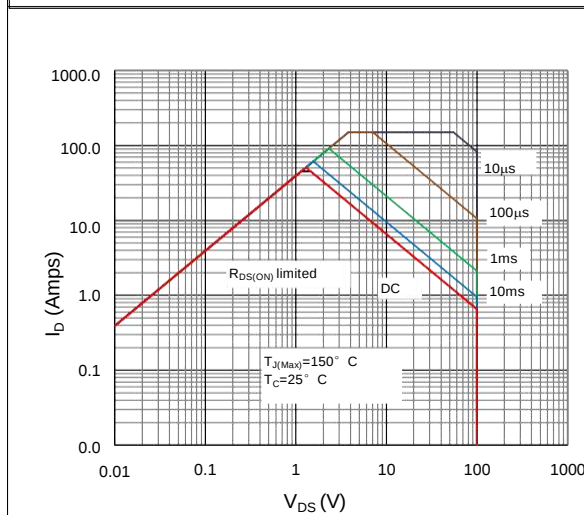


Figure 10. Maximum Drain Current vs. Case Temperature

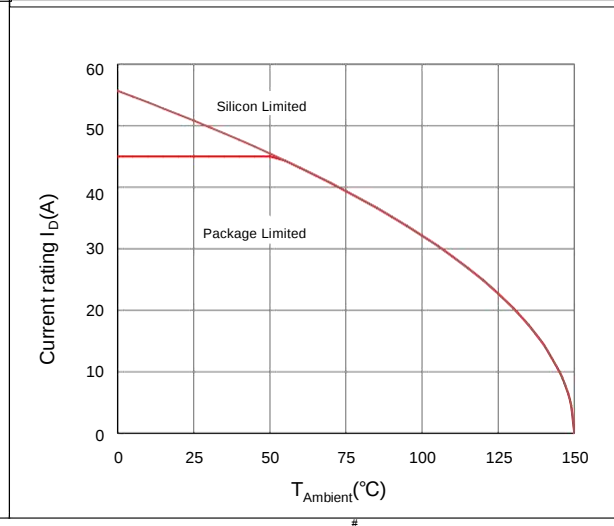
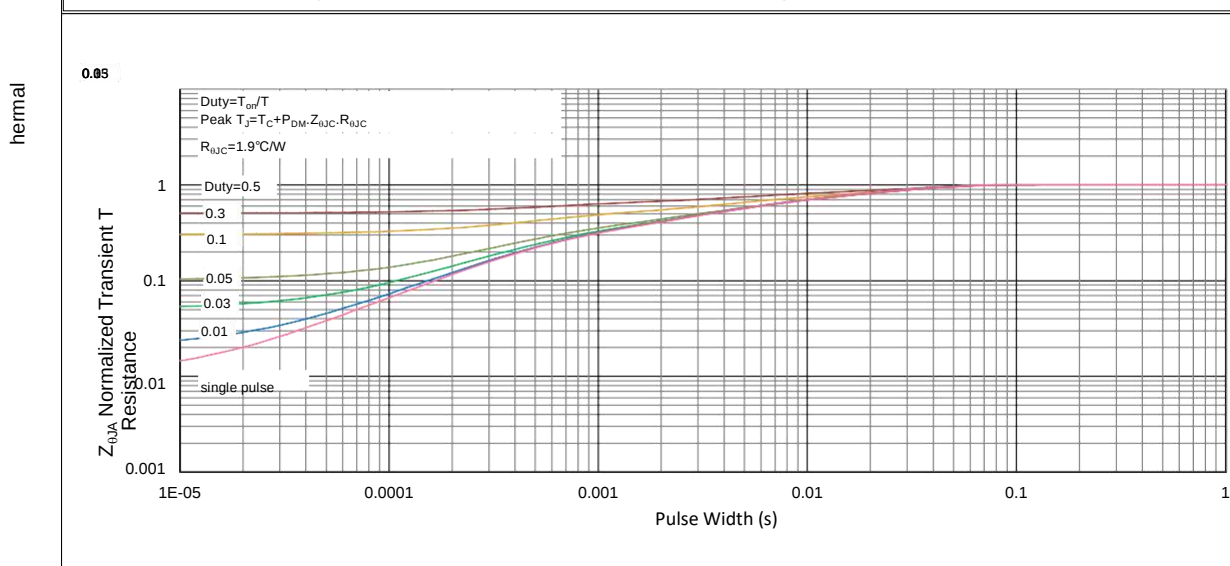
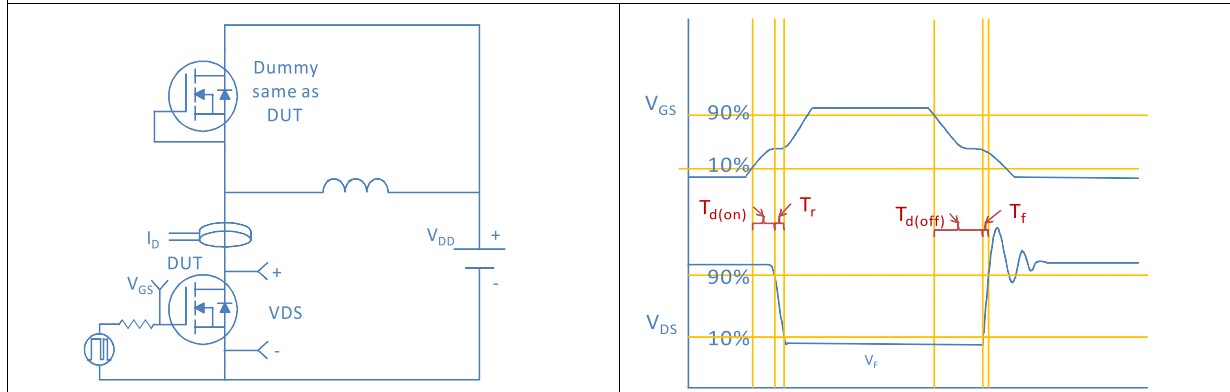


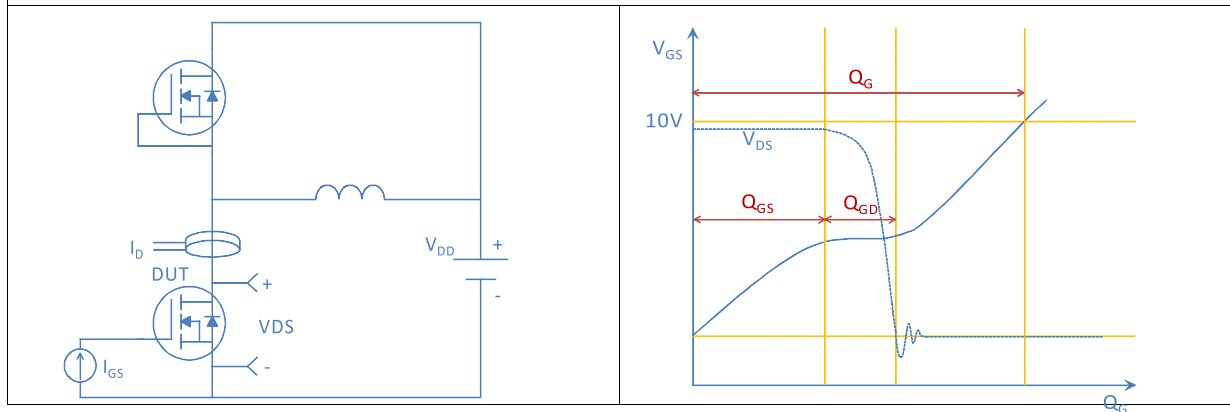
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient



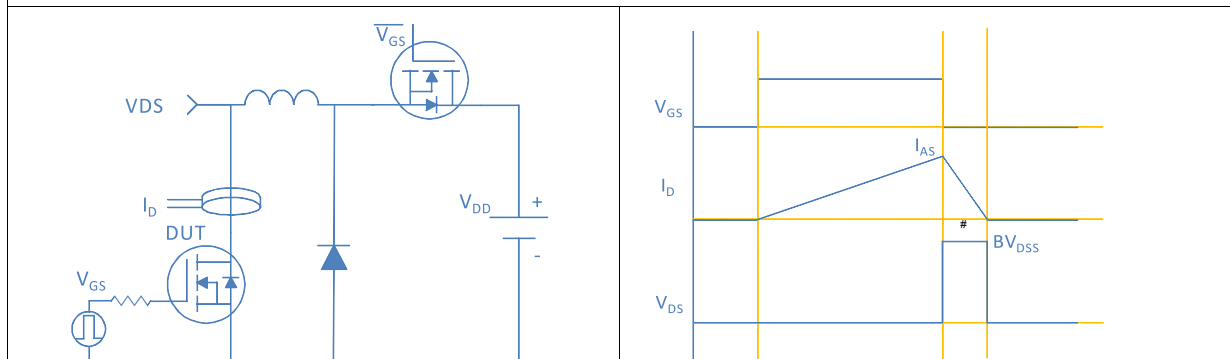
Inductive switching Test



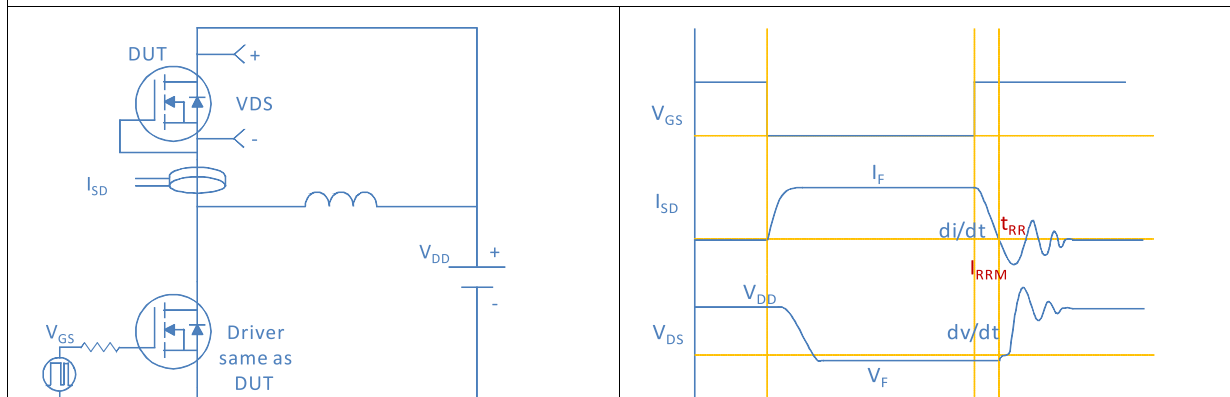
Gate Charge Test



Uclamped Inductive Switching (UIS) Test

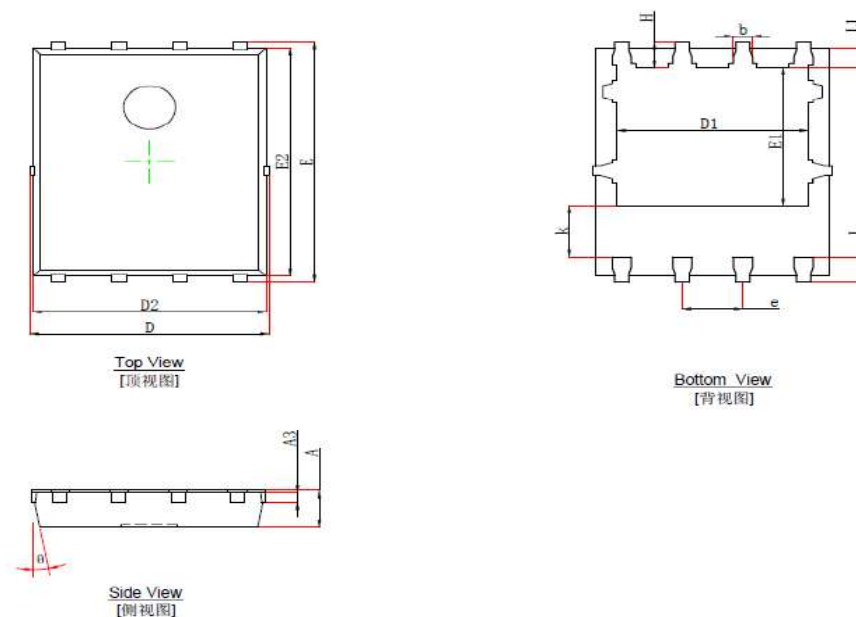


Diode Recovery Test



Package Outline

DFN5x6_P, 8 Leads



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A3	0.254 REF		0.010 REF	
D	4.680	5.120	0.184	0.202
E	5.900	6.126	0.232	0.241
D1	3.610	4.110	0.142	0.162
E1	3.380	3.780	0.133	0.149
D2	4.800	5.000	0.189	0.197
E2	5.674	5.826	0.223	0.229
k	1.100	1.390	0.043	0.055
b	0.330	0.510	0.013	0.020
e	1.270 TYP		1.270 TYP	
L	0.510	0.711	0.020	0.028
L1	0.424	0.576	0.017	0.023
H	0.410	0.726	0.016	0.029
ø	0°	12°	0°	12°